



STB30NS15

N-CHANNEL 150V - 0.075 Ω - 30A D²PAK LOW GATE CHARGE STripFET™ POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STB30NS15	150 V	<0.1 Ω	30 A

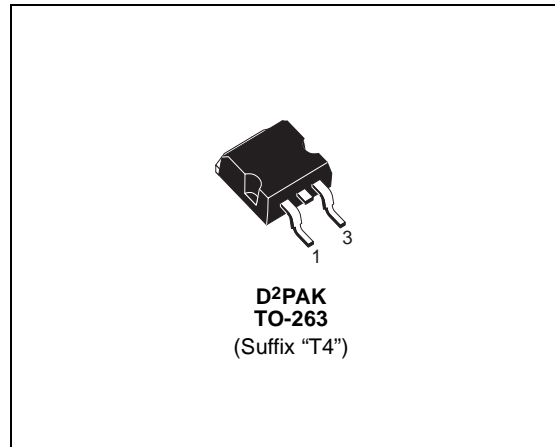
- TYPICAL R_{DS(on)} = 0.075 Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- APPLICATION ORIENTED CHARACTERIZATION
- FOR THROUGH-HOLE VERSION CONTACT SALES OFFICE

DESCRIPTION

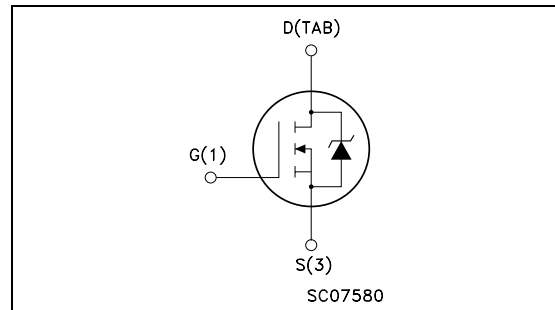
This MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency, high-frequency isolated DC-DC converters for Telecom and Computer applications. It is also intended for any applications with low gate drive requirements.

APPLICATIONS

- HIGH-EFFICIENCY DC-DC CONVERTERS
- UPS AND MOTOR CONTROL



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	150	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	150	V
V _{GS}	Gate- source Voltage	± 20	V
I _D	Drain Current (continuous) at T _C = 25°C	30	A
I _D	Drain Current (continuous) at T _C = 100°C	21	A
I _{DM} (●)	Drain Current (pulsed)	120	A
P _{tot}	Total Dissipation at T _C = 25°C	110	W
	Derating Factor	0.73	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	2	V/ns
EAS (2)	Single Pulse Avalanche Energy	250	mJ
T _{stg}	Storage Temperature	-55 to 175	°C
T _j	Max. Operating Junction Temperature		

● Pulse width limited by safe operating area.

(1) I_{SD} ≤ 30A, di/dt ≤ 100A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}.
(2) Starting T_j = 25 °C, I_D = 15A, V_{DD} = 25V

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THERMAL DATA

Rthj-case	Thermal Resistance Junction-case	Max	1.36	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	62.5	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		300	°C

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	150			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125°C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20V			±100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	2	3	4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 15 A		0.075	0.1	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} = 20 V I _D = 15 A		8		S
C _{iSS}	Input Capacitance	V _{DS} = 25V f = 1 MHz V _{GS} = 0		990		pF
C _{oss}	Output Capacitance			175		pF
C _{rSS}	Reverse Transfer Capacitance			110		pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 75\text{ V}$ $I_D = 15\text{ A}$		12		ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 3)		28		ns
Q_g	Total Gate Charge	$V_{DD} = 120\text{ V}$ $I_D = 30\text{ A}$ $V_{GS} = 10\text{ V}$		64		nC
Q_{gs}	Gate-Source Charge			8		nC
Q_{gd}	Gate-Drain Charge			27		nC

SWITCHING OFF(*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off Delay Time	$V_{DD} = 75\text{ V}$ $I_D = 15\text{ A}$		50		ns
t_f	Fall Time	$R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 3)		12		ns
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{clamp} = 120\text{ V}$ $I_D = 30\text{ A}$		50		ns
t_f	Fall Time	$R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$		17		ns
t_c	Cross-over Time	(Inductive Load, Figure 5)		11		ns

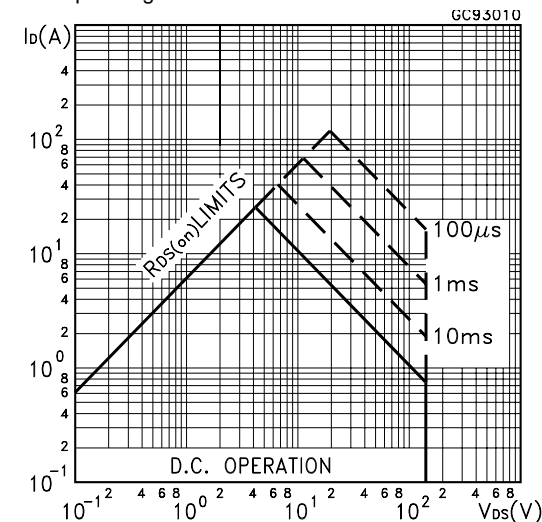
SOURCE DRAIN DIODE(*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				30	A
$I_{SDM} (\bullet)$	Source-drain Current (pulsed)				120	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 30\text{ A}$ $V_{GS} = 0$			1.3	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 30\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$		190		ns
Q_{rr}	Reverse Recovery Charge	$V_{DD} = 50\text{ V}$ $T_j = 150^\circ\text{C}$		1.25		μC
I_{RRM}	Reverse Recovery Current	(see test circuit, Figure 5)		13		A

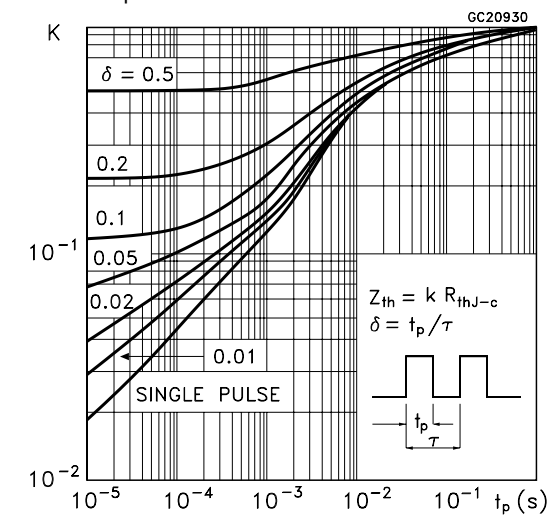
(*)Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

(\bullet)Pulse width limited by T_{jmax}

Safe Operating Area

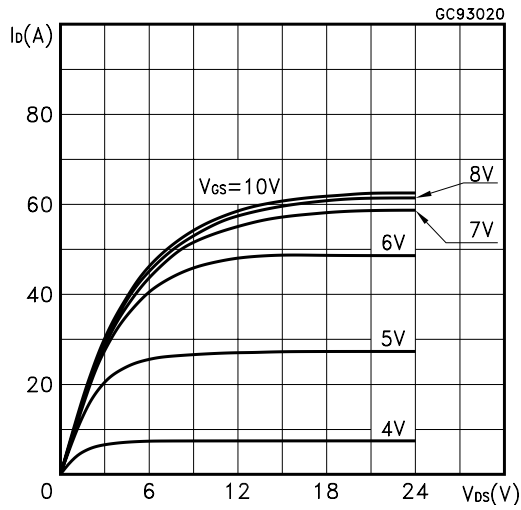


Thermal Impedance

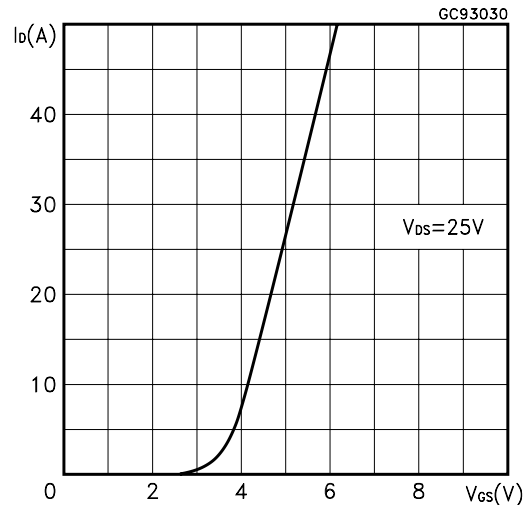


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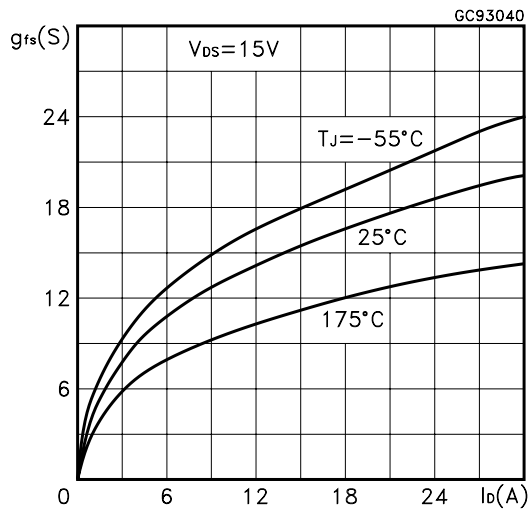
Output Characteristics



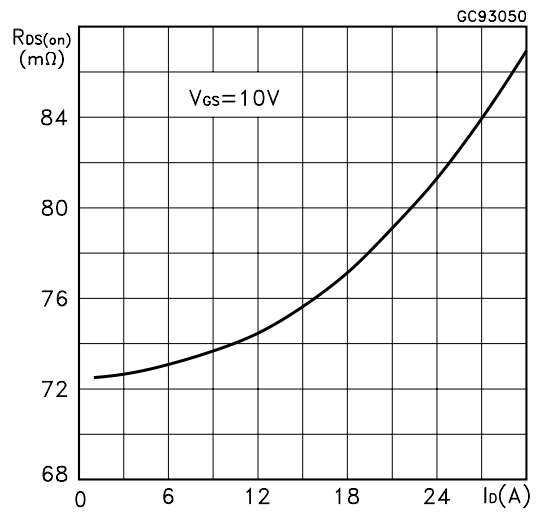
Transfer Characteristics



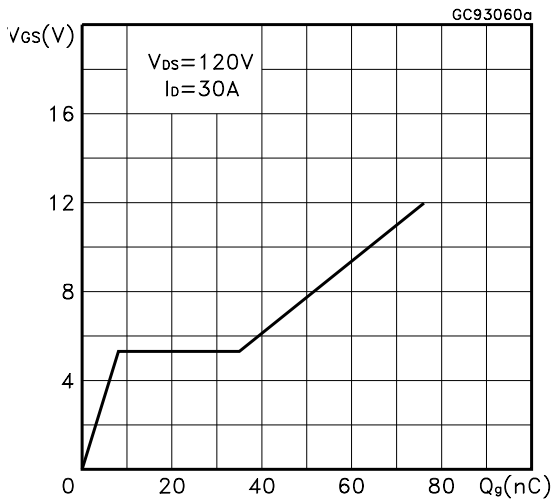
Transconductance



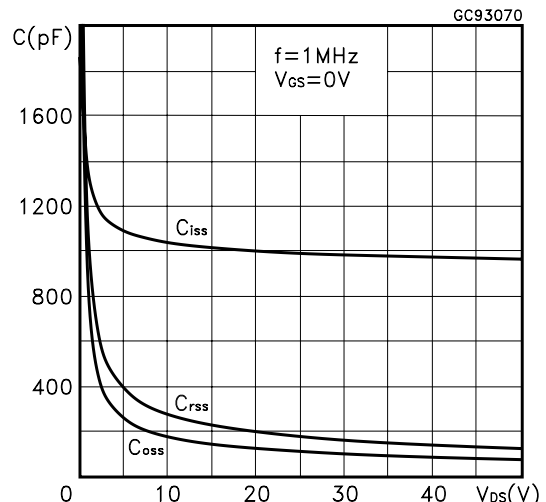
Static Drain-source On Resistance



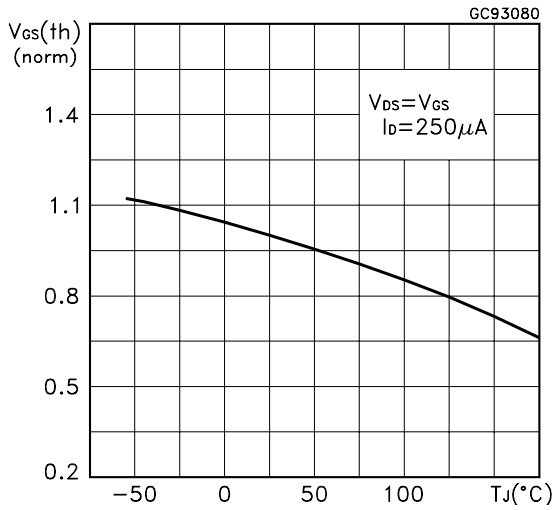
Gate Charge vs Gate-source Voltage



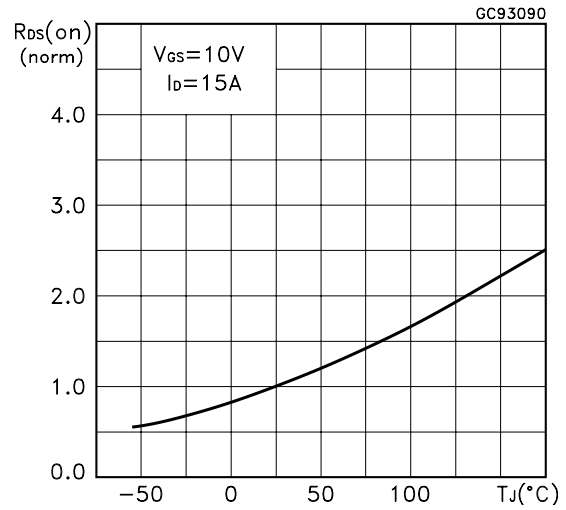
Capacitance Variations



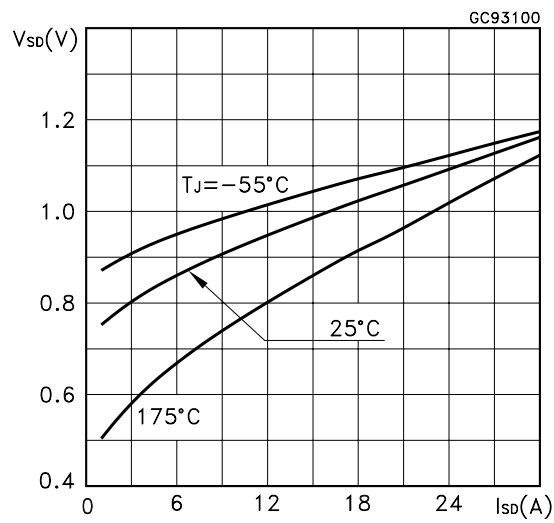
Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized Breakdown Voltage vs Temperature.

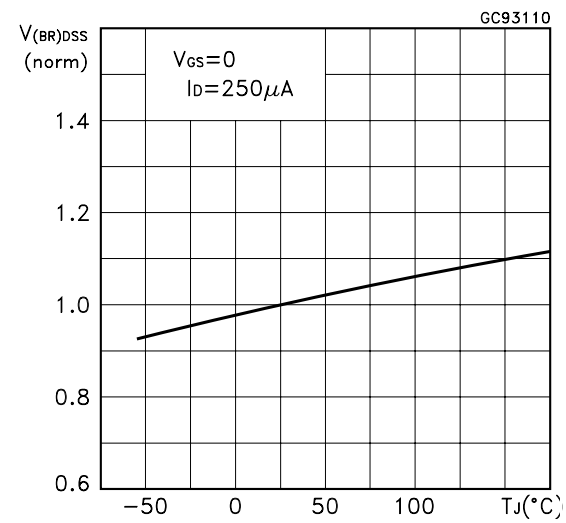


Fig. 1: Unclamped Inductive Load Test Circuit

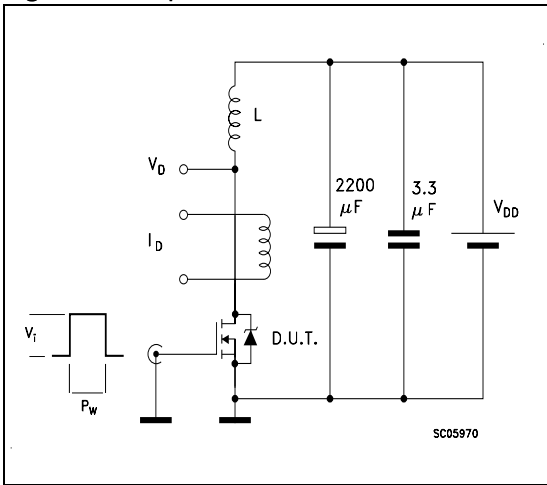


Fig. 2: Unclamped Inductive Waveform

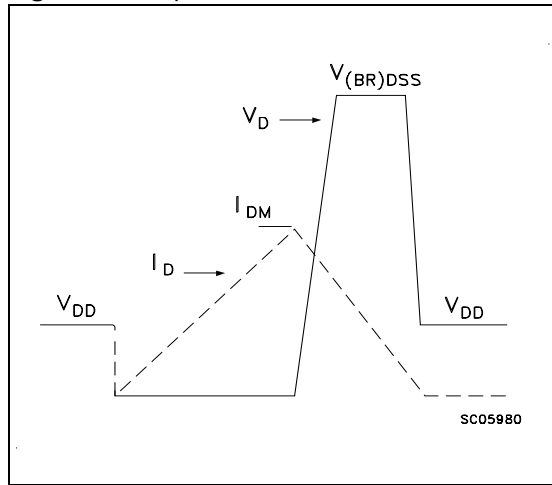


Fig. 3: Switching Times Test Circuits For Resistive Load

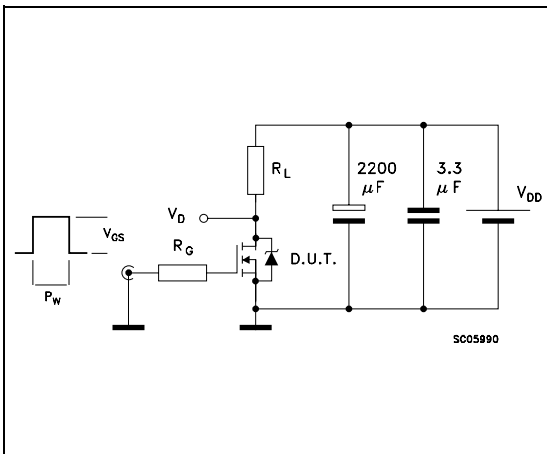


Fig. 4: Gate Charge test Circuit

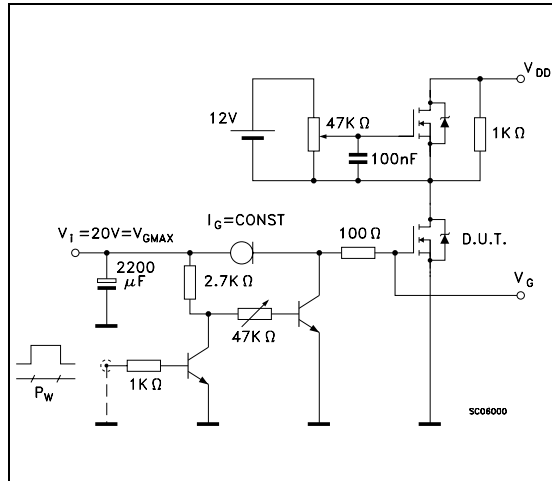
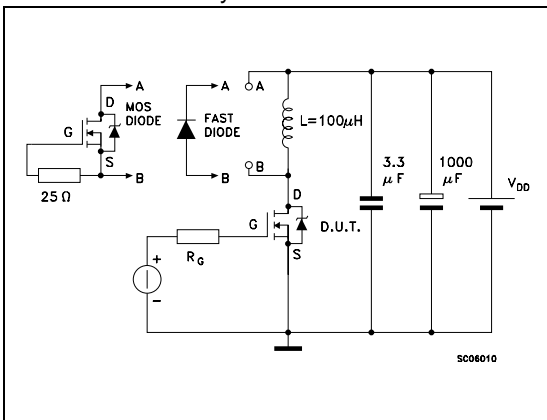
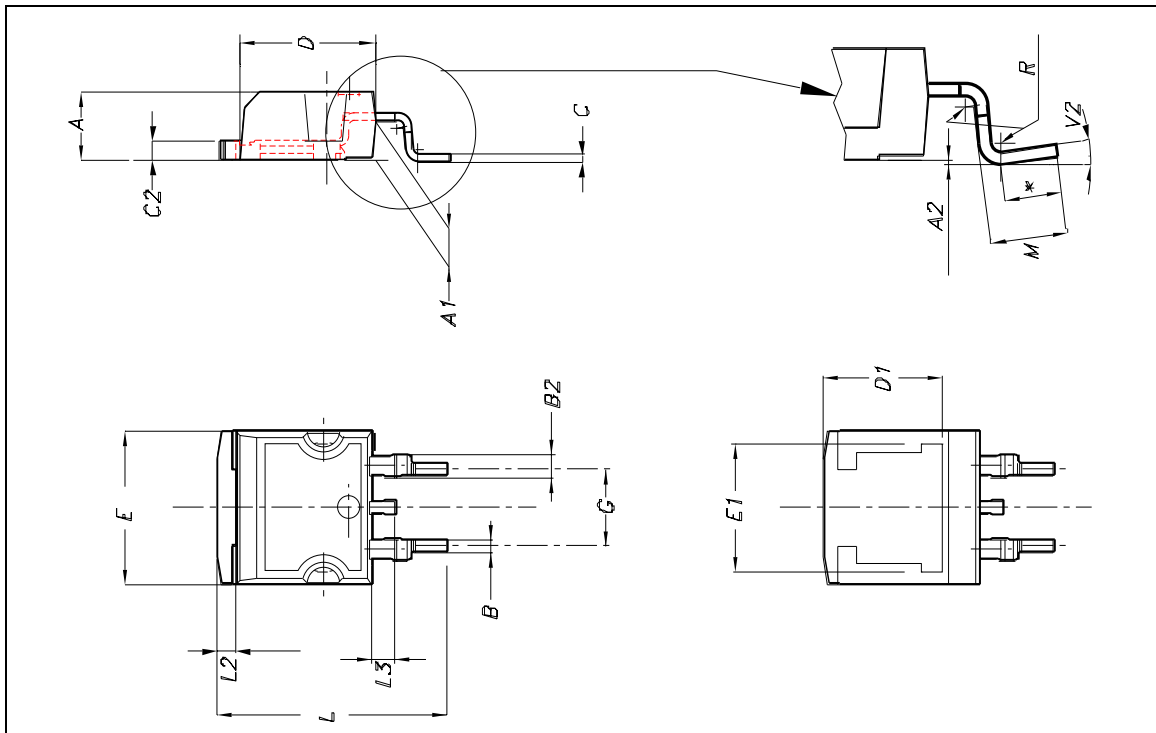


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times

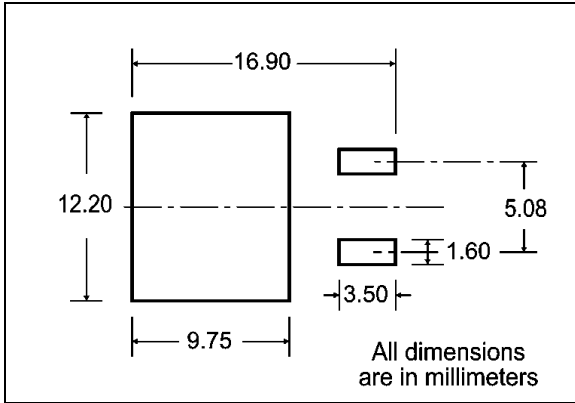


D²PAK MECHANICAL DATA

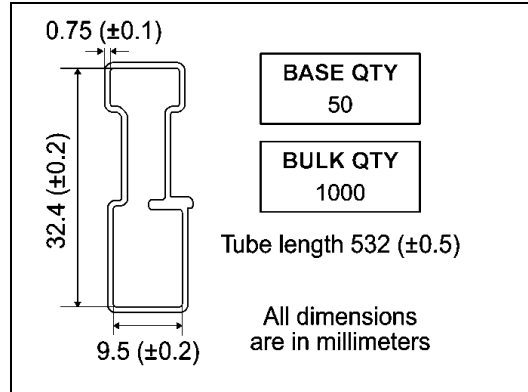
DIM.	mm.			inch.		
	MIN.	TYP.	MAX.	MIN.	TYP.	TYP.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.028		0.037
B2	1.14		1.7	0.045		0.067
C	0.45		0.6	0.018		0.024
C2	1.21		1.36	0.048		0.054
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.394		0.409
E1	8.5				0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.591		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.069
M	2.4		3.2	0.094		0.126
R		0.4			0.016	
V2	0°		8°	0°		8°



D2PAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	.00098	0.0137
W	23.7	24.3	0.933	0.956

TOP COVER TAPE

Center line of cavity

User Direction of Feed

FEED DIRECTION

Bending radius R min.

* on sales type

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